Microchip Technology - AGLN060V5-ZCSG81I Datasheet

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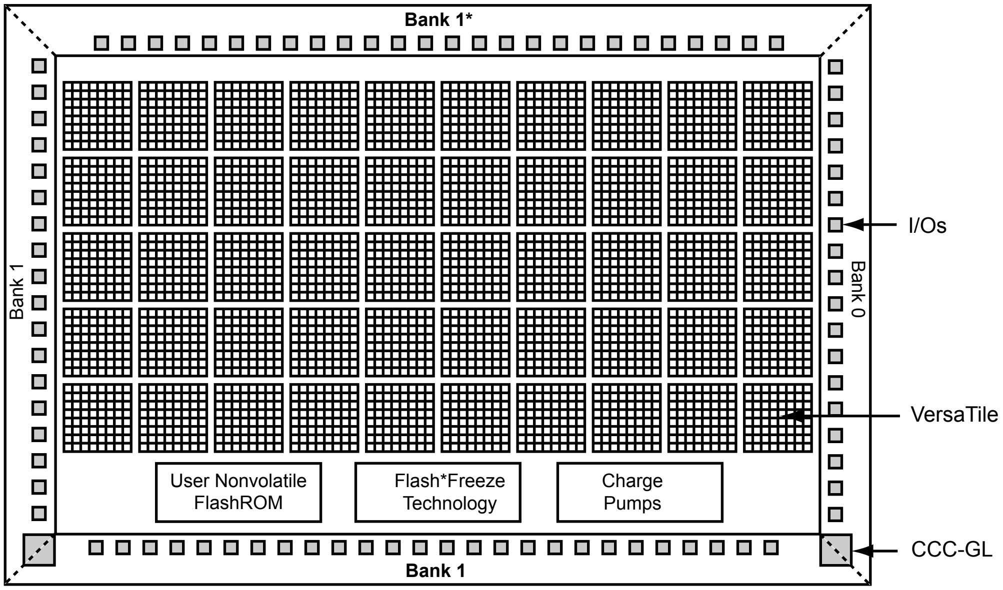
Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	1536
Total RAM Bits	18432
Number of I/O	60
Number of Gates	60000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	81-WFBGA, CSBGA
Supplier Device Package	81-CSP (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agln060v5-zcsg81i



Note: **Bank 0 for the AGLN030 device*

Figure 1-1 • **IGLOO Device Architecture Overview with Two I/O Banks and No RAM (AGLN010 and AGLN030)**

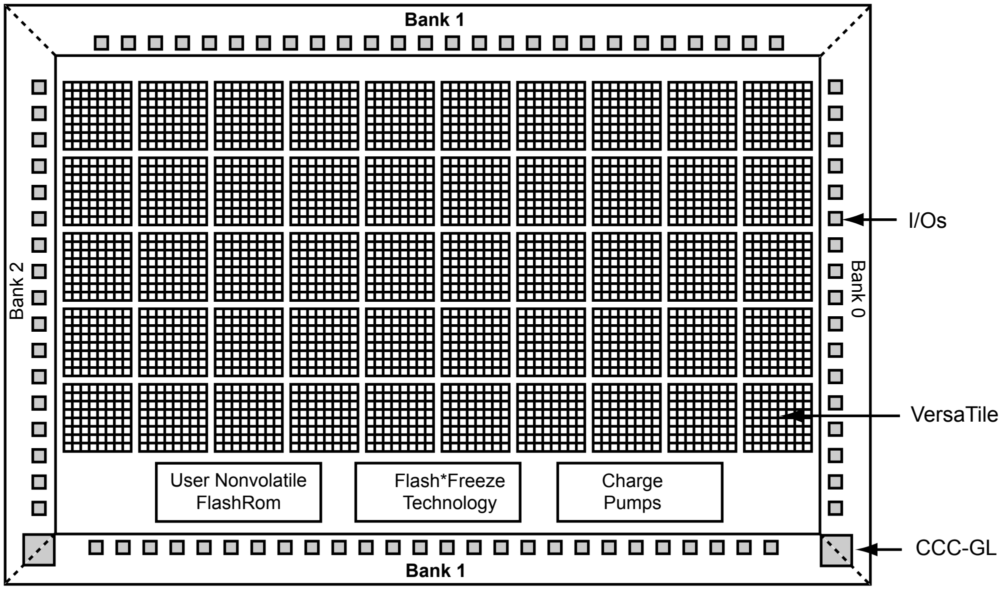


Figure 1-2 • **IGLOO Device Architecture Overview with Three I/O Banks and No RAM (AGLN015 and AGLN020)**

6. Click **OK** to return to the FlashPoint – Programming File Generator window.

Note: I/O States During programming are saved to the ADB and resulting programming files after completing programming file generation.

Table 2-10 • **Quiescent Supply Current (IDD) Characteristics, IGLOO nano Sleep Mode***

	Core Voltage	AGLN010	AGLN015	AGLN020	AGLN060	AGLN125	AGLN250	Units
VCCI= 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	1.7	1.7	1.7	µA
VCCI = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	1.8	1.8	1.8	µA
VCCI = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	1.9	1.9	1.9	µA
VCCI = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	2.2	2.2	2.2	µA
VCCI = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	2.5	2.5	2.5	µA

Note: *$I_{DD} = N_{BANKS} * I_{CCI}$.

Table 2-11 • **Quiescent Supply Current (IDD) Characteristics, IGLOO nano Shutdown Mode**

	Core Voltage	AGLN010	AGLN015	AGLN020	AGLN060	AGLN125	AGLN250	Units
Typical (25°C)	1.2 V / 1.5 V	0	0	0	0	0	0	µA

Table 2-12 • **Quiescent Supply Current (IDD), No IGLOO nano Flash*Freeze Mode[1]**

	Core Voltage	AGLN010	AGLN015	AGLN020	AGLN060	AGLN125	AGLN250	Units
ICCA Current[2]								
Typical (25°C)	1.2 V	3.7	5	5	10	13	18	µA
	1.5 V	8	14	14	20	28	44	µA
ICCI or IJTAG Current								
VCCI / VJTAG = 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	1.7	1.7	1.7	µA
VCCI / VJTAG = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	1.8	1.8	1.8	µA
VCCI / VJTAG = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	1.9	1.9	1.9	µA
VCCI / VJTAG = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	2.2	2.2	2.2	µA
VCCI / VJTAG = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	2.5	2.5	2.5	µA

Notes:

1. *IDD = N_{BANKS} * ICCI + ICCA. JTAG counts as one bank when powered.*
2. *Includes VCC, VCCPLL, and VPUMP currents.*

Guidelines

Toggle Rate Definition

A toggle rate defines the frequency of a net or logic element relative to a clock. It is a percentage. If the toggle rate of a net is 100%, this means that this net switches at half the clock frequency. Below are some examples:

- The average toggle rate of a shift register is 100% because all flip-flop outputs toggle at half of the clock frequency.
- The average toggle rate of an 8-bit counter is 25%:
  - Bit 0 (LSB) = 100%
  - Bit 1 = 50%
  - Bit 2 = 25%
  - …
  - Bit 7 (MSB) = 0.78125%
  - Average toggle rate = (100% + 50% + 25% + 12.5% + . . . + 0.78125%) / 8

Enable Rate Definition

Output enable rate is the average percentage of time during which tristate outputs are enabled. When nontristate output buffers are used, the enable rate should be 100%.

Table 2-19 • **Toggle Rate Guidelines Recommended for Power Calculation**

Component	Definition	Guideline
α_1	Toggle rate of VersaTile outputs	10%
α_2	I/O buffer toggle rate	10%

Table 2-20 • **Enable Rate Guidelines Recommended for Power Calculation**

Component	Definition	Guideline
β_1	I/O output buffer enable rate	100%
β_2	RAM enable rate for read operations	12.5%
β_3	RAM enable rate for write operations	12.5%

Applies to IGLOO nano at 1.5 V Core Operating Conditions

Table 2-25 • **Summary of I/O Timing Characteristics—Software Default Settings**
STD Speed Grade, Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

I/O Standard	Drive Strength (mA)	Equivalent Software Default Drive Strength Option[1]	Slew Rate	Capacitive Load (pF)	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	8 mA	High	5 pF	0.97	1.79	0.19	0.86	1.16	0.66	1.83	1.45	1.98	2.38	ns
3.3 V LVCMOS Wide Range[2]	100 µA	8 mA	High	5 pF	0.97	2.56	0.19	1.20	1.66	0.66	2.57	2.02	2.82	3.31	ns
2.5 V LVCMOS	8 mA	8 mA	High	5 pF	0.97	1.81	0.19	1.10	1.24	0.66	1.85	1.63	1.97	2.26	ns
1.8 V LVCMOS	4 mA	4 mA	High	5 pF	0.97	2.08	0.19	1.03	1.44	0.66	2.12	1.95	1.99	2.19	ns
1.5 V LVCMOS	2 mA	2 mA	High	5 pF	0.97	2.39	0.19	1.19	1.52	0.66	2.44	2.24	2.02	2.15	ns

Notes:

1. *The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range, as specified in the JESD8-B specification.*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Applies to IGLOO nano at 1.2 V Core Operating Conditions

Table 2-26 • **Summary of I/O Timing Characteristics—Software Default Settings
STD Speed Grade, Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V**

I/O Standard	Drive Strength (mA)	Equiv. Software Default Drive Strength Option[1]	Slew Rate	Capacitive Load (pF)	t_{DOUT}	t_{DP}	t_{DIN}	$t_{PY)}$	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	8 mA	High	5 pF	1.55	2.31	0.26	0.97	1.36	1.10	2.34	1.90	2.43	3.14	ns
3.3 V LVCMOS Wide Range[2]	100 µA	8 mA	High	5 pF	1.55	3.25	0.26	1.31	1.91	1.10	3.25	2.61	3.38	4.27	ns
2.5 V LVCMOS	8 mA	8 mA	High	5 pF	1.55	2.30	0.26	1.21	1.39	1.10	2.33	2.04	2.41	2.99	ns
1.8 V LVCMOS	4 mA	4 mA	High	5 pF	1.55	2.49	0.26	1.13	1.59	1.10	2.53	2.34	2.42	2.81	ns
1.5 V LVCMOS	2 mA	2 mA	High	5 pF	1.55	2.78	0.26	1.27	1.77	1.10	2.82	2.62	2.44	2.74	ns
1.2 V LVCMOS	1 mA	1 mA	High	5 pF	1.55	3.50	0.26	1.56	2.27	1.10	3.37	3.10	2.55	2.66	ns
1.2 V LVCMOS Wide Range[3]	100 µA	1 mA	High	5 pF	1.55	3.50	0.26	1.56	2.27	1.10	3.37	3.10	2.55	2.66	ns

Notes:

1. *The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range, as specified in the JESD8-B specification.*
3. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V side range as specified in the JESD8-12 specification.*
4. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Applies to 1.2 V DC Core Voltage

Table 2-49 • **2.5 LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	1.55	4.61	0.26	1.21	1.39	1.10	4.55	4.61	2.15	2.43	ns
4 mA	STD	1.55	4.61	0.26	1.21	1.39	1.10	4.55	4.61	2.15	2.43	ns
6 mA	STD	1.55	3.86	0.26	1.21	1.39	1.10	3.82	3.86	2.41	2.89	ns
8 mA	STD	1.55	3.86	0.26	1.21	1.39	1.10	3.82	3.86	2.41	2.89	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-50 • **2.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	1.55	2.68	0.26	1.21	1.39	1.10	2.72	2.54	2.15	2.51	ns
4 mA	STD	1.55	2.68	0.26	1.21	1.39	1.10	2.72	2.54	2.15	2.51	ns
6 mA	STD	1.55	2.30	0.26	1.21	1.39	1.10	2.33	2.04	2.41	2.99	ns
8 mA	STD	1.55	2.30	0.26	1.21	1.39	1.10	2.33	2.04	2.41	2.99	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Fully Registered I/O Buffers with Asynchronous Clear

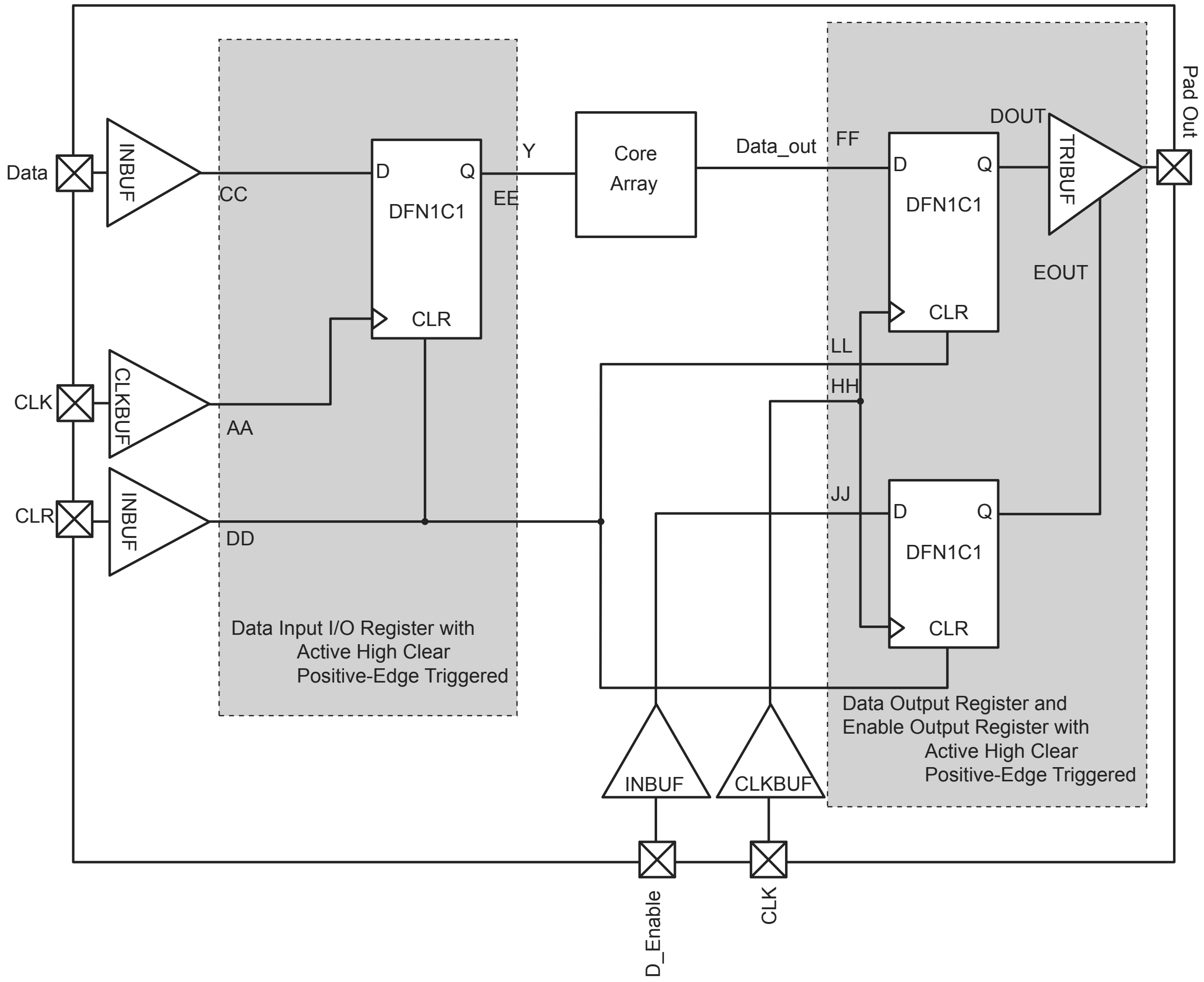


Figure 2-13 **• Timing Model of the Registered I/O Buffers with Asynchronous Clear**

1.2 V DC Core Voltage

Table 2-75 • Output Data Register Propagation Delays
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{OCLKQ}	Clock-to-Q of the Output Data Register	1.52	ns
t_{OSUD}	Data Setup Time for the Output Data Register	1.15	ns
t_{OHD}	Data Hold Time for the Output Data Register	0.00	ns
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	1.96	ns
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	1.96	ns
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	0.24	ns
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	0.24	ns
t_{OWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Data Register	0.19	ns
t_{OWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Data Register	0.19	ns
$t_{OCKMPWH}$	Clock Minimum Pulse Width HIGH for the Output Data Register	0.31	ns
$t_{OCKMPWL}$	Clock Minimum Pulse Width LOW for the Output Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

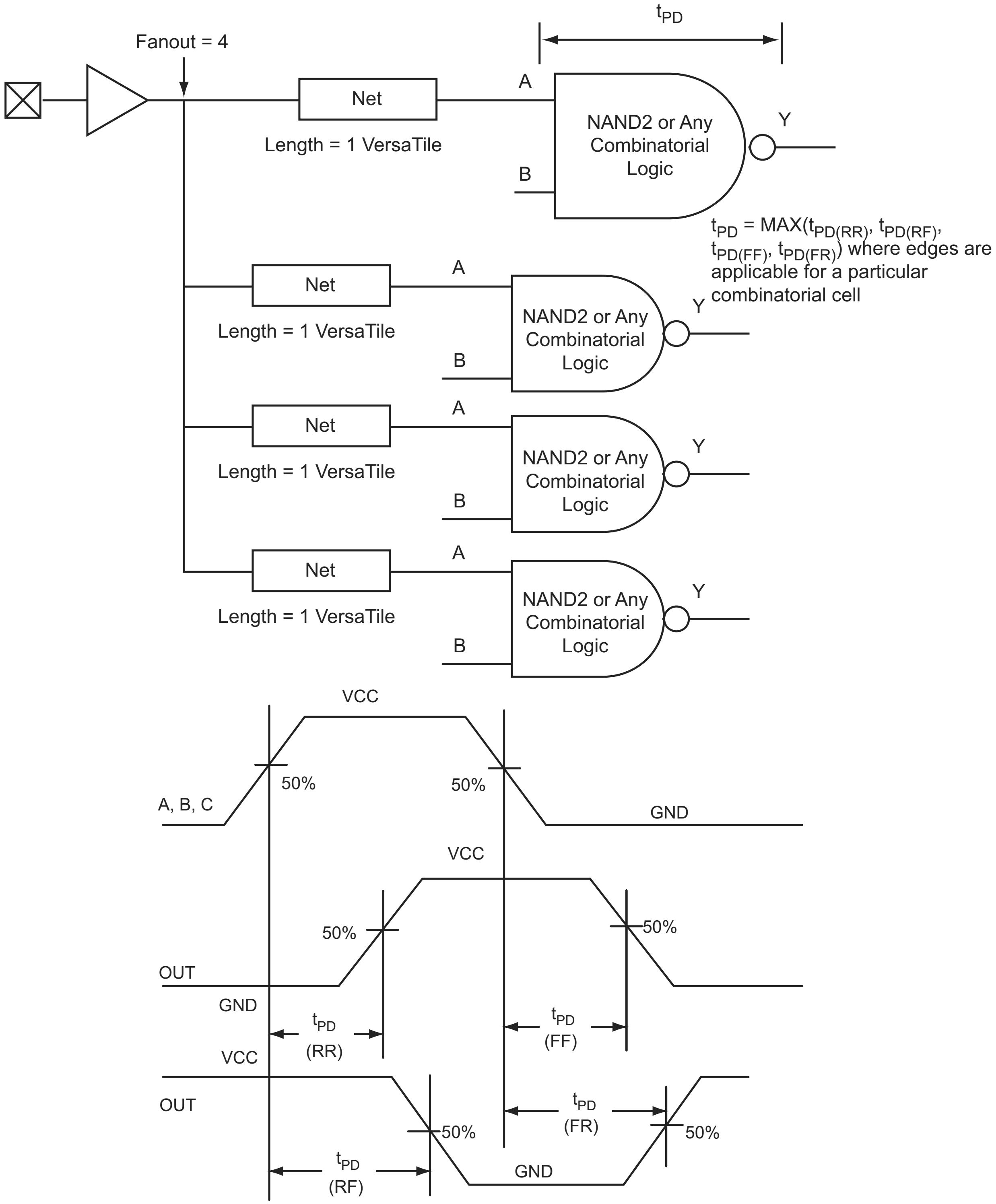


***Figure 2-22* • Timing Model and Waveforms**

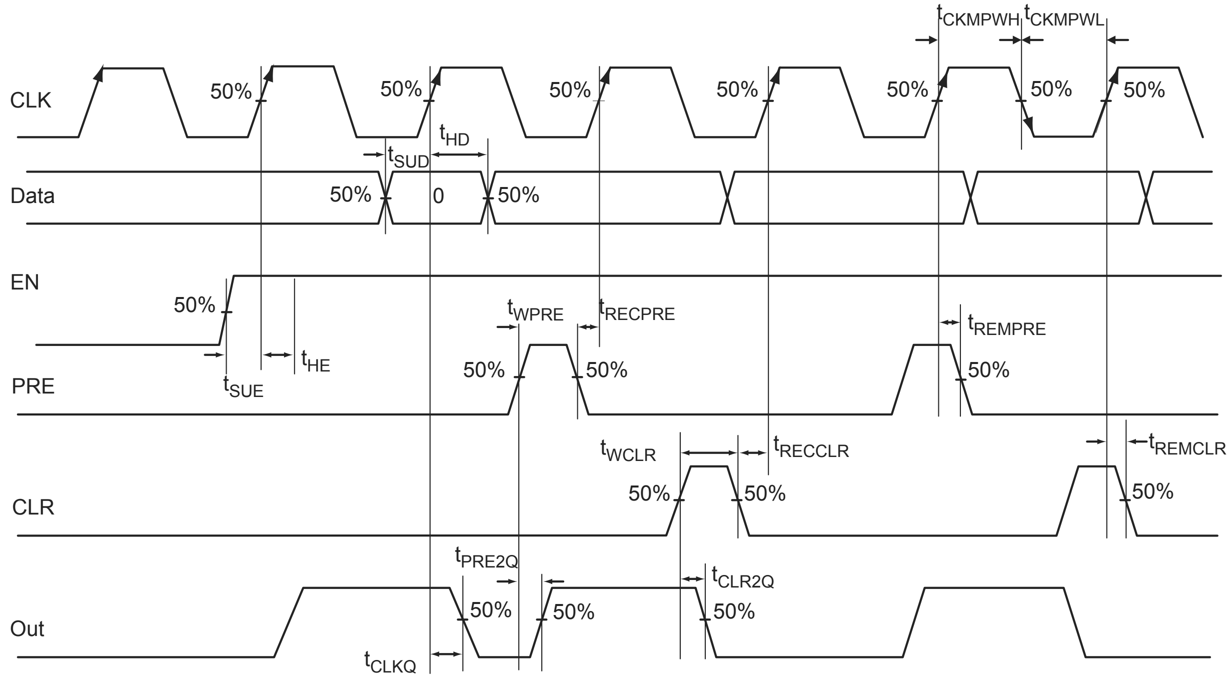


Figure 2-24 • **Timing Model and Waveforms**

Timing Characteristics

1.5 V DC Core Voltage

Table 2-86 • **Register Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{CLKQ}	Clock-to-Q of the Core Register	0.89	ns
t_{SUD}	Data Setup Time for the Core Register	0.81	ns
t_{HD}	Data Hold Time for the Core Register	0.00	ns
t_{SUE}	Enable Setup Time for the Core Register	0.73	ns
t_{HE}	Enable Hold Time for the Core Register	0.00	ns
t_{CLR2Q}	Asynchronous Clear-to-Q of the Core Register	0.60	ns
t_{PRE2Q}	Asynchronous Preset-to-Q of the Core Register	0.62	ns
t_{REMCLR}	Asynchronous Clear Removal Time for the Core Register	0.00	ns
t_{RECCLR}	Asynchronous Clear Recovery Time for the Core Register	0.24	ns
t_{REMPRE}	Asynchronous Preset Removal Time for the Core Register	0.00	ns
t_{RECPRE}	Asynchronous Preset Recovery Time for the Core Register	0.23	ns
t_{WCLR}	Asynchronous Clear Minimum Pulse Width for the Core Register	0.30	ns
t_{WPRE}	Asynchronous Preset Minimum Pulse Width for the Core Register	0.30	ns
t_{CKMPWH}	Clock Minimum Pulse Width HIGH for the Core Register	0.56	ns
t_{CKMPWL}	Clock Minimum Pulse Width LOW for the Core Register	0.56	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Timing Characteristics

1.5 V DC Core Voltage

Table 2-102 • **RAM4K9**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	0.69	ns
t_{AH}	Address hold time	0.13	ns
t_{ENS}	REN, WEN setup time	0.68	ns
t_{ENH}	REN, WEN hold time	0.13	ns
t_{BKS}	BLK setup time	1.37	ns
t_{BKH}	BLK hold time	0.13	ns
t_{DS}	Input data (DIN) setup time	0.59	ns
t_{DH}	Input data (DIN) hold time	0.30	ns
t_{CKQ1}	Clock HIGH to new data valid on DOUT (output retained, WMODE = 0)	2.94	ns
	Clock HIGH to new data valid on DOUT (flow-through, WMODE = 1)	2.55	ns
t_{CKQ2}	Clock HIGH to new data valid on DOUT (pipelined)	1.51	ns
t_{C2CWWL}[1]	Address collision clk-to-clk delay for reliable write after write on same address; applicable to closing edge	0.23	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address; applicable to opening edge	0.35	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address; applicable to opening edge	0.41	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	1.72	ns
	RESET Low to data out Low on DOUT (pipelined)	1.72	ns
$t_{REMRSTB}$	RESET removal	0.51	ns
$t_{RECRSTB}$	RESET recovery	2.68	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.68	ns
t_{CYC}	Clock cycle time	6.24	ns
F_{MAX}	Maximum frequency	160	MHz

Notes:

1. *For more information, refer to the application note AC374: Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based FPGAs and SoC FPGAs App Note.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Timing Waveforms

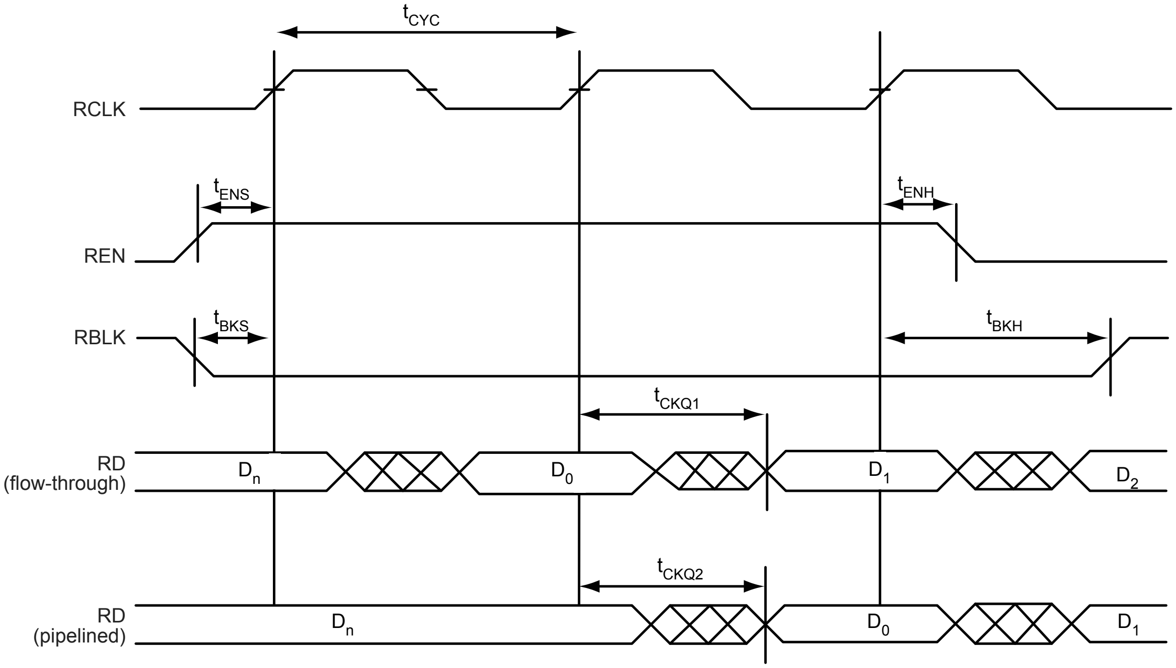


Figure 2-34 **• FIFO Read**

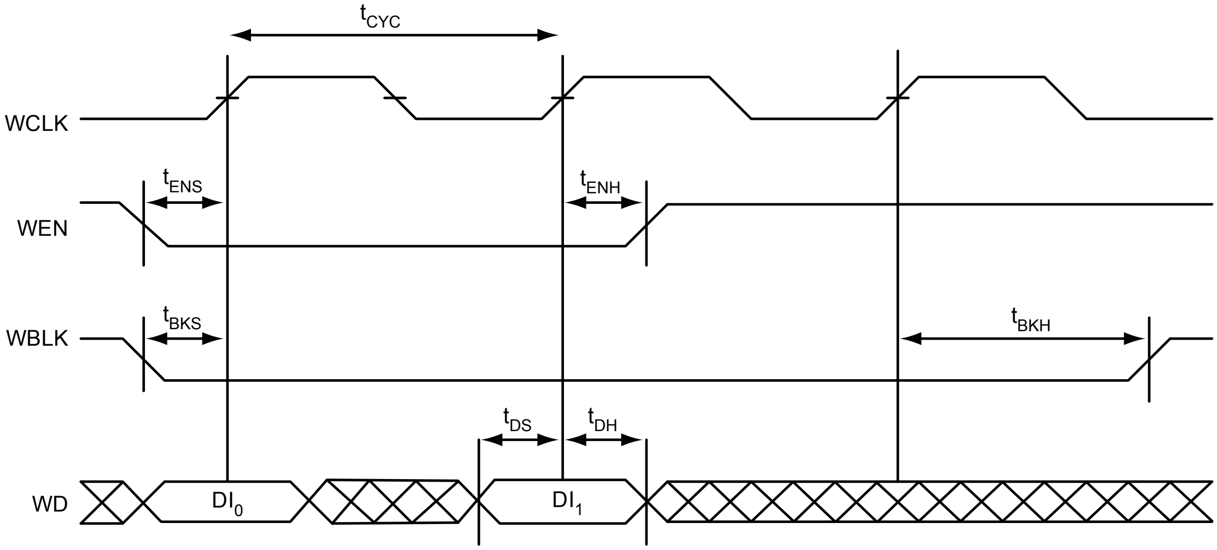


Figure 2-35 **• FIFO Write**

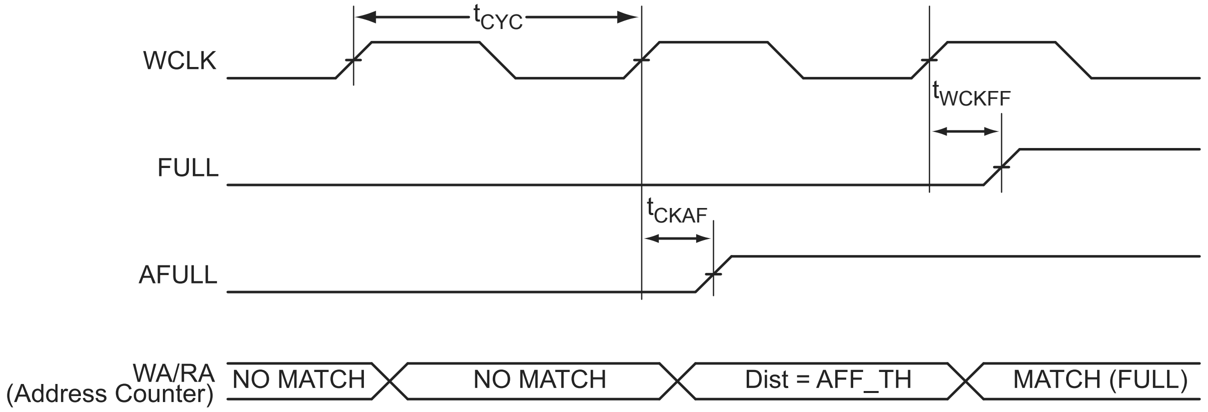


Figure 2-38 • **FIFO FULL Flag and AFULL Flag Assertion**

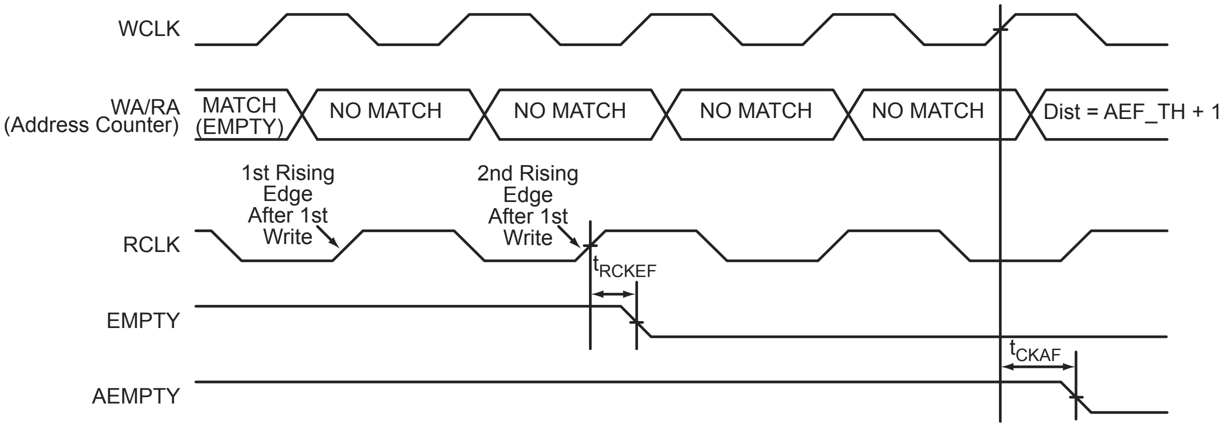


Figure 2-39 • **FIFO EMPTY Flag and AEMPTY Flag Deassertion**

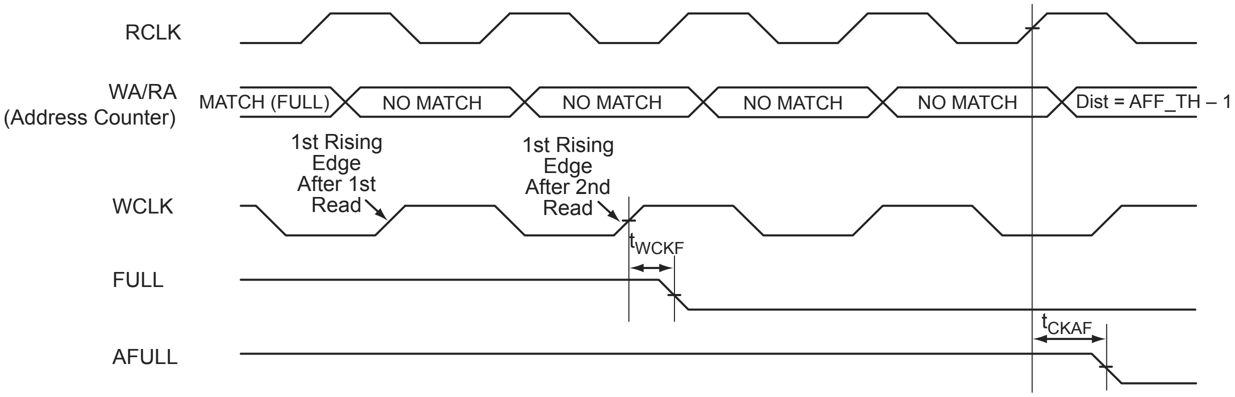


Figure 2-40 • **FIFO FULL Flag and AFULL Flag Deassertion**

JTAG 1532 Characteristics

JTAG timing delays do not include JTAG I/Os. To obtain complete JTAG timing, add I/O buffer delays to the corresponding standard selected; refer to the I/O timing characteristics in the "User I/O Characteristics" section on page 2-15 for more details.

Timing Characteristics

1.5 V DC Core Voltage

***Table 2-110* • JTAG 1532**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{DISU}	Test Data Input Setup Time	1.00	ns
t_{DIHD}	Test Data Input Hold Time	2.00	ns
t_{TMSSU}	Test Mode Select Setup Time	1.00	ns
t_{TMDHD}	Test Mode Select Hold Time	2.00	ns
t_{TCK2Q}	Clock to Q (data out)	8.00	ns
t_{RSTB2Q}	Reset to Q (data out)	25.00	ns
F_{TCKMAX}	TCK Maximum Frequency	15	MHz
$t_{TRSTREM}$	ResetB Removal Time	0.58	ns
$t_{TRSTREC}$	ResetB Recovery Time	0.00	ns
$t_{TRSTMPW}$	ResetB Minimum Pulse	TBD	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

1.2 V DC Core Voltage

***Table 2-111* • JTAG 1532**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{DISU}	Test Data Input Setup Time	1.50	ns
t_{DIHD}	Test Data Input Hold Time	3.00	ns
t_{TMSSU}	Test Mode Select Setup Time	1.50	ns
t_{TMDHD}	Test Mode Select Hold Time	3.00	ns
t_{TCK2Q}	Clock to Q (data out)	11.00	ns
t_{RSTB2Q}	Reset to Q (data out)	30.00	ns
F_{TCKMAX}	TCK Maximum Frequency	9.00	MHz
$t_{TRSTREM}$	ResetB Removal Time	1.18	ns
$t_{TRSTREC}$	ResetB Recovery Time	0.00	ns
$t_{TRSTMPW}$	ResetB Minimum Pulse	TBD	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

3 – Pin Descriptions

Supply Pins

GND Ground

Ground supply voltage to the core, I/O outputs, and I/O logic.

GNDQ Ground (quiet)

Quiet ground supply voltage to input buffers of I/O banks. Within the package, the GNDQ plane is decoupled from the simultaneous switching noise originated from the output buffer ground domain. This minimizes the noise transfer within the package and improves input signal integrity. GNDQ must always be connected to GND on the board.

VCC Core Supply Voltage

Supply voltage to the FPGA core, nominally 1.5 V for IGLOO nano V5 devices, and 1.2 V or 1.5 V for IGLOO nano V2 devices. VCC is required for powering the JTAG state machine in addition to VJTAG. Even when a device is in bypass mode in a JTAG chain of interconnected devices, both VCC and VJTAG must remain powered to allow JTAG signals to pass through the device.

VCCIBx I/O Supply Voltage

Supply voltage to the bank's I/O output buffers and I/O logic. Bx is the I/O bank number. There are up to eight I/O banks on low power flash devices plus a dedicated VJTAG bank. Each bank can have a separate VCCI connection. All I/Os in a bank will run off the same VCCIBx supply. VCCI can be 1.2 V, 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VCCI pins tied to GND.

VMVx I/O Supply Voltage (quiet)

Quiet supply voltage to the input buffers of each I/O bank. *x* is the bank number. Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks. This minimizes the noise transfer within the package and improves input signal integrity. Each bank must have at least one VMV connection, and no VMV should be left unconnected. All I/Os in a bank run off the same VMVx supply. VMV is used to provide a quiet supply voltage to the input buffers of each I/O bank. VMVx can be 1.2 V, 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VMV pins tied to GND. VMV and VCCI should be at the same voltage within a given I/O bank. Used VMV pins must be connected to the corresponding VCCI pins of the same bank (i.e., VMV0 to VCCIB0, VMV1 to VCCIB1, etc.).

VCCPLA/B/C/D/E/F PLL Supply Voltage

Supply voltage to analog PLL, nominally 1.5 V or 1.2 V.

When the PLLs are not used, the Microsemi Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground. Microsemi recommends tying VCCPLx to VCC and using proper filtering circuits to decouple VCC noise from the PLLs. Refer to the PLL Power Supply Decoupling section of the "Clock Conditioning Circuits in IGLOO and ProASIC3 Devices" chapter in the *IGLOO nano FPGA Fabric User's Guide* for a complete board solution for the PLL analog power supply and ground.

There is one VCCPLF pin on IGLOO nano devices.

VCOMPLA/B/C/D/E/F PLL Ground

Ground to analog PLL power supplies. When the PLLs are not used, the Microsemi Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground.

There is one VCOMPLF pin on IGLOO nano devices.

VJTAG JTAG Supply Voltage

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG

CS81	
Pin Number	**AGLN250 Function**
A1	GAA0/IO00RSB0
A2	GAA1/IO01RSB0
A3	GAC0/IO04RSB0
A4	IO07RSB0
A5	IO09RSB0
A6	IO12RSB0
A7	GBB0/IO16RSB0
A8	GBA1/IO19RSB0
A9	GBA2/IO20RSB1
B1	GAA2/IO67RSB3
B2	GAB0/IO02RSB0
B3	GAC1/IO05RSB0
B4	IO06RSB0
B5	IO10RSB0
B6	GBC0/IO14RSB0
B7	GBB1/IO17RSB0
B8	IO21RSB1
B9	GBB2/IO22RSB1
C1	GAB2/IO65RSB3
C2	IO66RSB3
C3	GND
C4	IO08RSB0
C5	IO11RSB0
C6	GND
C7	GBA0/IO18RSB0
C8	GBC2/IO23RSB1
C9	IO24RSB1
D1	GAC2/IO63RSB3
D2	IO64RSB3
D3	GFA2/IO56RSB3
D4	VCC
D5	VCCIB0
D6	GND
D7	IO30RSB1
D8	GCC1/IO25RSB1
D9	GCC0/IO26RSB1
E1	GFB0/IO59RSB3
E2	GFB1/IO60RSB3
E3	GFA1/IO58RSB3
E4	VCCIB3
E5	VCC
E6	VCCIB1
E7	GCA0/IO28RSB1
E8	GCA1/IO27RSB1
E9	GCB2/IO29RSB1
F1	VCCPLF
F2	VCOMPLF
F3	GND
F4	GND
F5	VCCIB2
F6	GND
F7	GDA1/IO33RSB1
F8	GDC1/IO31RSB1
F9	GDC0/IO32RSB1
G1	GEA0/IO51RSB3
G2	GEC1/IO54RSB3
G3	GEC0/IO53RSB3
G4	IO45RSB2
G5	IO42RSB2
G6	IO37RSB2
G7	GDB2/IO35RSB2
G8	VJTAG
G9	TRST
H1	GEA1/IO52RSB3
H2	FF/GEB2/IO49RSB2
H3	IO47RSB2
H4	IO44RSB2
H5	IO41RSB2
H6	IO39RSB2
H7	GDA2/IO34RSB2
H8	TDI
H9	TDO
J1	GEA2/IO50RSB2
J2	GEC2/IO48RSB2
J3	IO46RSB2
J4	IO43RSB2
J5	IO40RSB2
J6	IO38RSB2
J7	TCK
J8	TMS
J9	VPUMP

*Note: * Pin numbers F1 and F2 must be connected to ground because a PLL is not supported for AGLN250-CS81.*

QN68	
Pin Number	AGLN020 Function
1	IO60RSB2
2	IO54RSB2
3	IO52RSB2
4	IO50RSB2
5	IO49RSB2
6	GEC0/IO48RSB2
7	GEA0/IO47RSB2
8	VCC
9	GND
10	VCCIB2
11	IO46RSB2
12	IO45RSB2
13	IO44RSB2
14	IO43RSB2
15	IO42RSB2
16	IO41RSB2
17	IO40RSB2
18	FF/IO39RSB1
19	IO37RSB1
20	IO35RSB1
21	IO33RSB1
22	IO31RSB1
23	IO30RSB1
24	VCC
25	GND
26	VCCIB1
27	IO27RSB1
28	IO25RSB1
29	IO23RSB1
30	IO21RSB1
31	IO19RSB1
32	TCK
33	TDI
34	TMS
35	VPUMP

QN68	
Pin Number	AGLN020 Function
36	TDO
37	TRST
38	VJTAG
39	IO17RSB0
40	IO16RSB0
41	GDA0/IO15RSB0
42	GDC0/IO14RSB0
43	IO13RSB0
44	VCCIB0
45	GND
46	VCC
47	IO12RSB0
48	IO11RSB0
49	IO09RSB0
50	IO05RSB0
51	IO00RSB0
52	IO07RSB0
53	IO03RSB0
54	IO18RSB1
55	IO20RSB1
56	IO22RSB1
57	IO24RSB1
58	IO28RSB1
59	NC
60	GND
61	NC
62	IO32RSB1
63	IO34RSB1
64	IO36RSB1
65	IO61RSB2
66	IO58RSB2
67	IO56RSB2
68	IO63RSB2

Revision / Version	Changes	Page
Revision 9 (Mar2010) Product Brief Advance v0.9 Packaging Advance v0.8	All product tables and pin tables were updated to show clearly that AGLN030 is available only in the Z feature grade at this time. The nano-Z feature grade devices are designated with a Z at the end of the part number.	N/A
Revision 8 (Jan 2009)	The "Reprogrammable Flash Technology" section was revised to add "250 MHz (1.5 V systems) and 160 MHz (1.2 V systems) System Performance".	I
Product Brief Advance v0.8	The note for AGLN030 in the "IGLOO nano Devices" table and "I/Os Per Package" table was revised to remove the statement regarding package compatibility with lower density nano devices.	II, II
	The "I/Os with Advanced I/O Standards" section was revised to add definitions for hot-swap and cold-sparing.	1-8
Packaging Advance v0.7	The "UC81", "CS81", "QN48", and "QN68" pin tables for AGLN030 are new.	4-5, 4-8, 4-17, 4-21
	The "CS81"pin table for AGLN060 is new.	4-9
	The "CS81" and "VQ100" pin tables for AGLN060Z are new.	4-10, 4-25
	The "CS81" and "VQ100" pin tables for AGLN125Z are new.	4-12, 4-27
	The "CS81" and "VQ100" pin tables for AGLN250Z is new.	4-14, 4-29
Revision 7 (Apr 2009) Product Brief Advance v0.7 DC and Switching Characteristics Advance v0.3	The –F speed grade is no longer offered for IGLOO nano devices and was removed from the datasheet.	N/A
Revision 6 (Mar 2009) Packaging Advance v0.6	The "VQ100" pin table for AGLN030 is new.	4-23
Revision 5 (Feb 2009) Packaging Advance v0.5	The "100-Pin QFN" section was removed.	N/A
Revision 4 (Feb 2009)	The QN100 package was removed for all devices.	N/A
Product Brief Advance v0.6	"IGLOO nano Devices" table was updated to change the maximum user I/Os for AGLN030 from 81 to 77.	II
	The "Device Marking" section is new.	V
Revision 3 (Feb 2009) Product Brief Advance v0.5	The following table note was removed from "IGLOO nano Devices" table: "Six chip (main) and three quadrant global networks are available for AGLN060 and above."	II
	The CS81 package was added for AGLN250 in the "IGLOO nano Products Available in the Z Feature Grade" table.	VI
Packaging Advance v0.4	The "UC81" and "CS81" pin tables for AGLN020 are new.	4-4, 4-7
	The "CS81" pin table for AGLN250 is new.	4-13

Revision / Version	Changes	Page
Revision 2 (Dec 2008) Product Brief Advance v0.4	The second table note in "IGLOO nano Devices" table was revised to state, "AGLN060, AGLN125, and AGLN250 in the CS81 package do not support PLLs. AGLN030 and smaller devices do not support this feature."	II
	The I/Os per package for CS81 were revised to 60 for AGLN060, AGLN125, and AGLN250 in the "I/Os Per Package"table.	II
Packaging Advance v0.3	The "UC36" pin table is new.	4-2
Revision 1 (Nov 2008) Product Brief Advance v0.3	The "Advanced I/Os" section was updated to include wide power supply voltage support for 1.14 V to 1.575 V.	I
	The AGLN030 device was added to product tables and replaces AGL030 entries that were formerly in the tables.	VI
	The "I/Os Per Package"table was updated for the CS81 package to change the number of I/Os for AGLN060, AGLN125, and AGLN250 from 66 to 64.	II
	The "Wide Range I/O Support" section is new.	1-8
	The table notes and references were revised in Table 2-2 • Recommended Operating Conditions [1]. VMV was included with VCCI and a table note was added stating, "VMV pins must be connected to the corresponding VCCI pins. See *Pin Descriptions* for further information." Please review carefully.	2-2
	VJTAG was added to the list in the table note for Table 2-9 • Quiescent Supply Current (IDD) Characteristics, IGLOO nano Flash*Freeze Mode*. Values were added for AGLN010, AGLN015, and AGLN030 for 1.5 V.	2-7
	VCCI was removed from the list in the table note for Table 2-10 • Quiescent Supply Current (IDD) Characteristics, IGLOO nano Sleep Mode*.	2-8
	Values for I_{CCA} current were updated for AGLN010, AGLN015, and AGLN030 in Table 2-12 • Quiescent Supply Current (IDD), No IGLOO nano Flash*Freeze Mode[1].	2-8
	Values for PAC1 and PAC2 were added to Table 2-15 • Different Components Contributing to Dynamic Power Consumption in IGLOO nano Devices and Table 2-17 • Different Components Contributing to Dynamic Power Consumption in IGLOO nano Devices.	2-10, 2-11
	Table notes regarding wide range support were added to Table 2-21 • Summary of Maximum and Minimum DC Input and Output Levels.	2-19
	1.2 V LVCMOS wide range values were added to Table 2-22 • Summary of Maximum and Minimum DC Input Levels and Table 2-23 • Summary of AC Measuring Points.	2-19, 2-20
	The following table note was added to Table 2-25 • Summary of I/O Timing Characteristics—Software Default Settings and Table 2-26 • Summary of I/O Timing Characteristics—Software Default Settings: "All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range, as specified in the JESD8-B specification."	2-21
	3.3 V LVCMOS Wide Range and 1.2 V Wide Range were added to Table 2-28 • I/O Output Buffer Maximum Resistances [1] andTable 2-30 • I/O Short Currents IOSH/IOSL.	2-23, 2-24